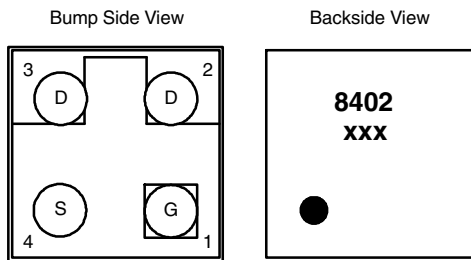


20 V N-Channel 1.8 V (G-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
20	0.037 at V _{GS} = 4.5 V	7.3
	0.039 at V _{GS} = 2.5 V	7.1
	0.043 at V _{GS} = 1.8 V	6.8

MICRO FOOT



Device Marking: 8402
xxx = Date/Lot Traceability Code

FEATURES

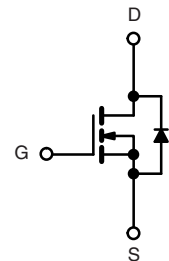
- TrenchFET[®] Power MOSFET
- MICRO FOOT[®] Chipscale Packaging Reduces Footprint Area Profile (0.62 mm) and On-Resistance Per Footprint Area
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- PA, Battery and Load Switch for Portable Devices



N-Channel MOSFET

Ordering Information: Si8402DB-T1-E1 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V _{DS}	20		V	
Gate-Source Voltage	V _{GS}	± 8			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	7.3	5.3	A
		T _A = 70 °C	5.9	4.3	
Pulsed Drain Current	I _{DM}	30		A	
Continuous Source Current (Diode Conduction) ^a	I _S	2.3	1.2		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	2.77	1.47	W
		T _A = 70 °C	1.77	0.94	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Package Reflow Conditions ^b	IR/Convection	260			

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 5 s	35	45	°C/W
		Steady State	72	85	
Maximum Junction-to-Foot (Drain)	R _{thJF}	16	20		

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
b. Refer to IPC/JEDEC (J-STD-020), no manual or hand soldering.

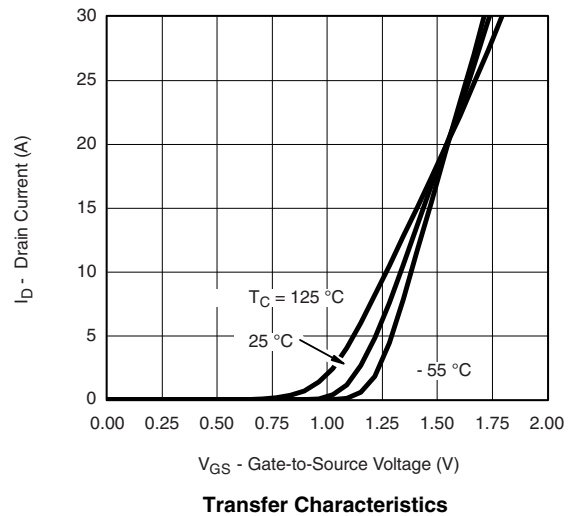
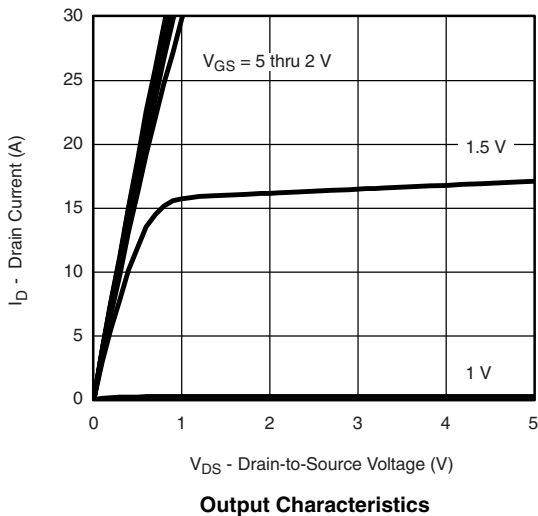
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.4		1	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq 5\text{ V}, V_{GS} = 4.5\text{ V}$	5			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 1\text{ A}$		0.031	0.037	Ω
		$V_{GS} = 2.5\text{ V}, I_D = 1\text{ A}$		0.033	0.039	
		$V_{GS} = 1.8\text{ V}, I_D = 1\text{ A}$		0.035	0.043	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 1\text{ A}$		12		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 1\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 1\text{ A}$		17	26	nC
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			3.1		
Gate Resistance	R_g	$f = 1\text{ MHz}$		15		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 6\text{ }\Omega$		30	45	ns
Rise Time	t_r			45	70	
Turn-Off Delay Time	$t_{d(off)}$			145	220	
Fall Time	t_f			75	115	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		30	60	

Notes:

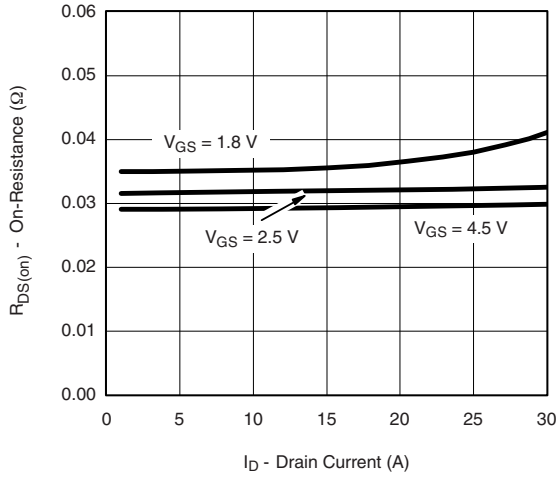
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

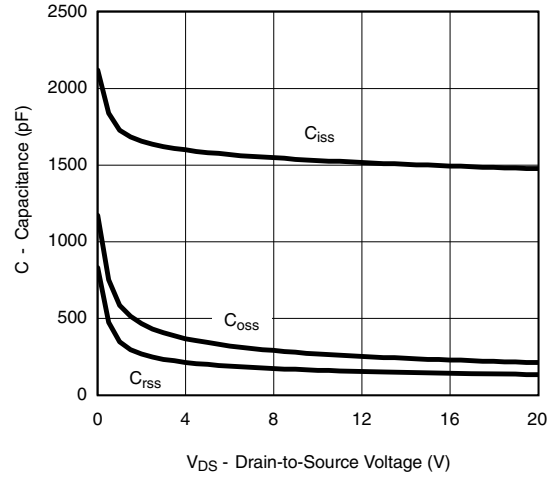
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



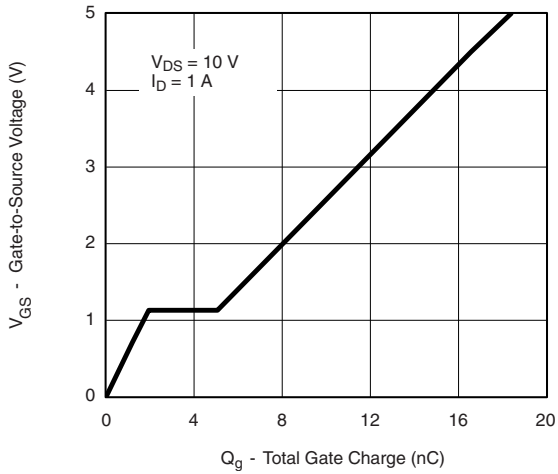
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



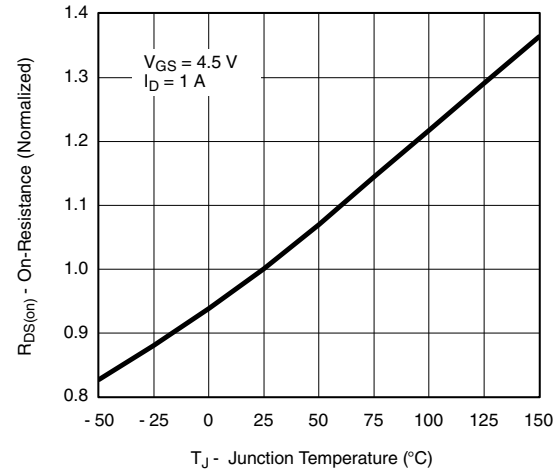
On-Resistance vs. Drain Current



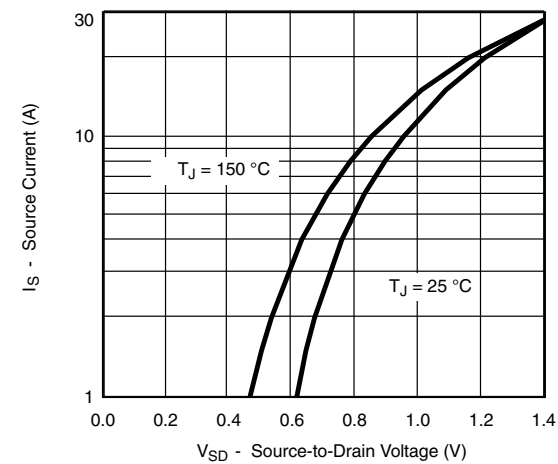
Capacitance



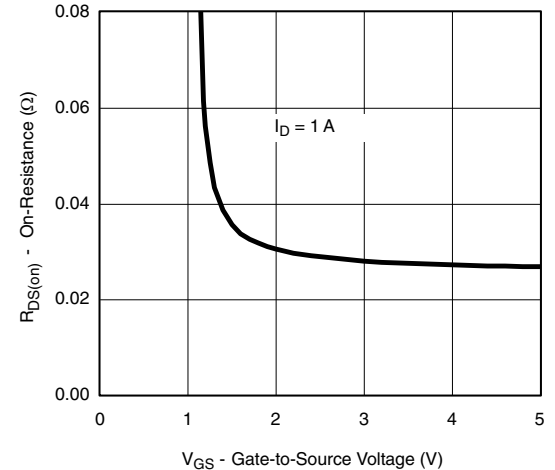
Gate Charge



On-Resistance vs. Junction Temperature

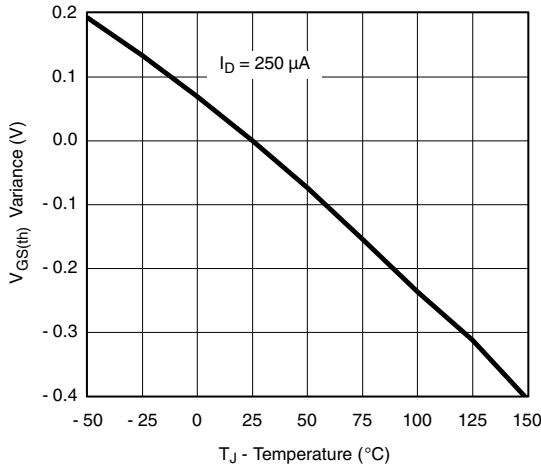


Source-Drain Diode Forward Voltage

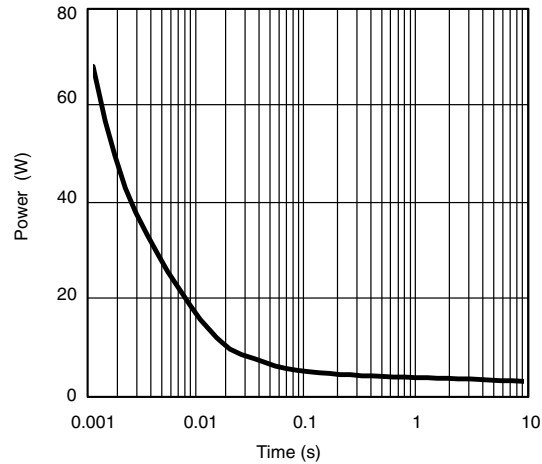


On-Resistance vs. Gate-to-Source Voltage

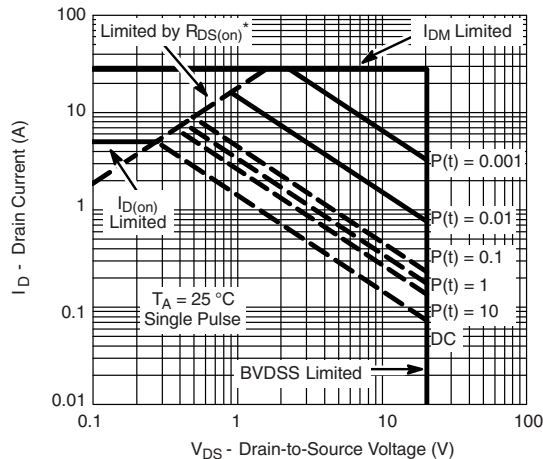
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Threshold Voltage

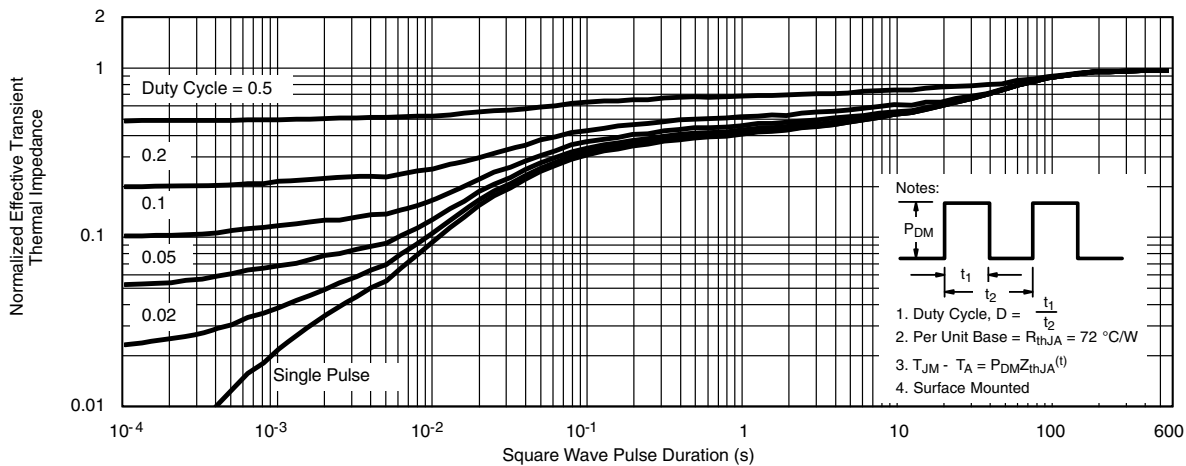


Single Pulse Power, Junction-to-Ambient



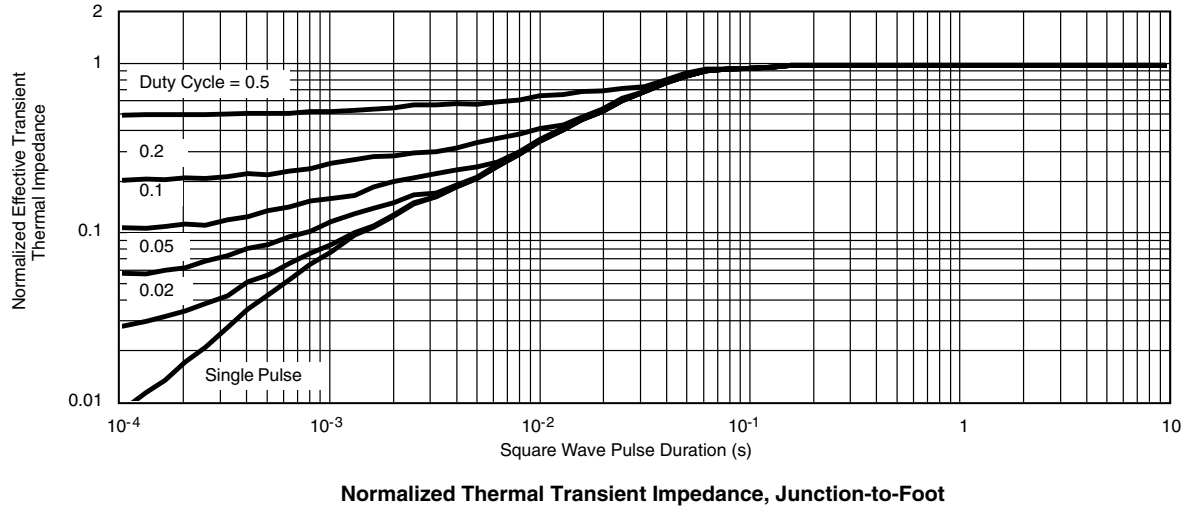
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area



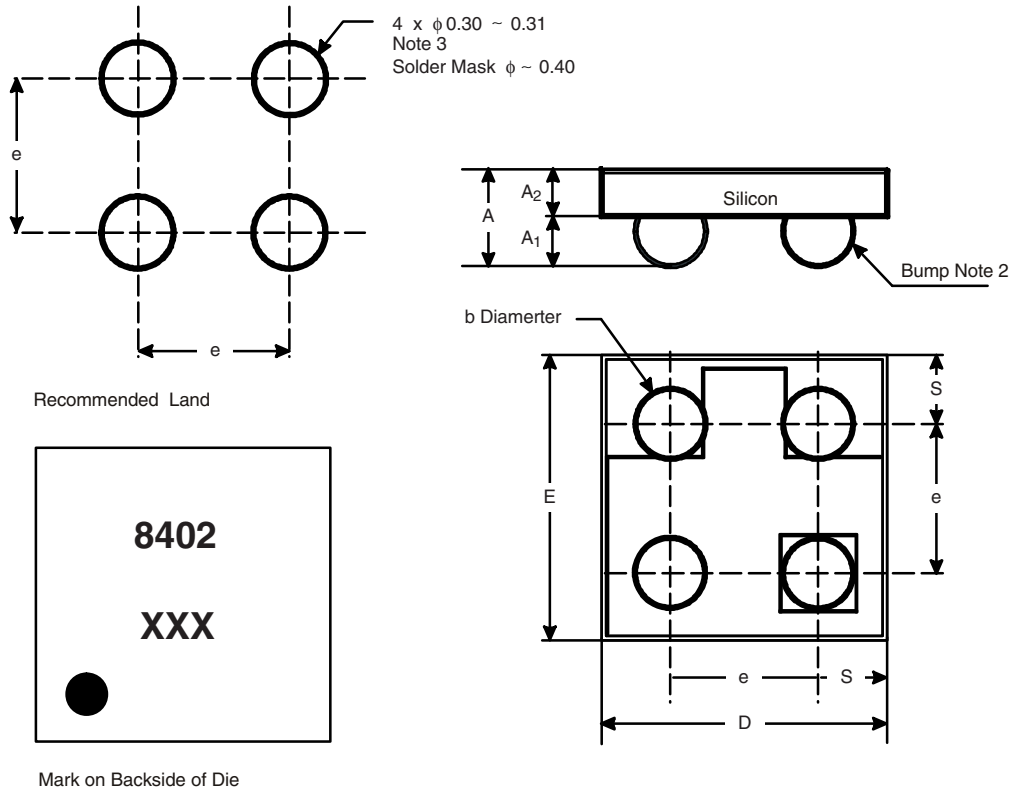
Normalized Thermal Transient Impedance, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



PACKAGE OUTLINE

MICRO FOOT: 4-BUMP (0.8 mm PITCH)



Notes (Unless Otherwise Specified):

1. Laser mark on the silicon die back, coated with a thin metal.
2. Bumps are 95.5/3.8/0.7 Sn/Ag/Cu.
3. Non-solder mask defined copper landing pad.
4. The flat side of wafers is oriented at the bottom.

Dim.	Millimeters ^a		Inches	
	Min.	Max.	Min.	Max.
A	0.600	0.650	0.0236	0.0256
A ₁	0.260	0.290	0.0102	0.0114
A ₂	0.340	0.360	0.0134	0.0142
b	0.370	0.410	0.0146	0.0161
D	1.520	1.600	0.0598	0.0630
E	1.520	1.600	0.0598	0.0630
e	0.800		0.0315	
S	0.360	0.400	0.0142	0.0157

Notes:

- a. Use millimeters as the primary measurement.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72657.



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.